

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



FDS6679

30 Volt P-Channel PowerTrench® MOSFET

General Description

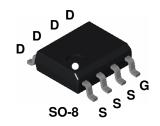
This P-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers, and battery chargers.

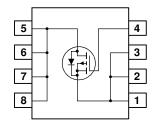
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\text{DS(ON)}}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- • -13 A, -30 V. $R_{DS(ON)} = 9$ m Ω @ $V_{GS} = -10$ V $R_{DS(ON)} = 13$ m Ω @ $V_{GS} = -4.5$ V
- $\bullet~$ Extended V_{GSS} range (±25V) for battery applications
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$
- · High power and current handling capability





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain-Source Voltage		-30	V	
V _{GSS}	Gate-Source Voltage		±25	V	
I _D	Drain Current - Continuous	(Note 1a)	-13	A	
	- Pulsed		-50		
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W	
		(Note 1b)	1.2		
		(Note 1c)	1.0		
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +175	°C	

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
R _θ JC	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6679	FDS6679	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1	l	I	l	,
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-30			V
$\Delta BV_{DSS} \over \Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		-23		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μА
I _{GSS}	Gate-Body Leakage	$V_{GS} = \pm 25 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			±100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	-1	-1.6	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		5		mV/°C
$R_{\text{DS}(\text{on})}$	Static Drain–Source On–Resistance	$\begin{split} V_{GS} &= -10 \text{ V}, & I_D = -13 \text{ A} \\ V_{GS} &= -4.5 \text{ V}, & I_D = -11 \text{ A} \\ V_{GS} &= -10 \text{ V}, I_D = -13 \text{ A}, T_J = 125 ^{\circ}\text{C} \end{split}$		7.3 10 9.5	9 13 13	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -10 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-50			Α
g _{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -13 \text{ A}$		44		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V},$		3939		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		972		pF
C _{rss}	Reverse Transfer Capacitance			498		pF
Switchir	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -15 \text{ V}, \qquad I_{D} = -1 \text{ A},$		19	34	ns
t _r	Turn-On Rise Time	$V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		10	20	ns
t _{d(off)}	Turn-Off Delay Time	1		110	176	ns
t _f	Turn-Off Fall Time	1		65	104	ns
Q _g	Total Gate Charge	$V_{DS} = -15 \text{ V}, \qquad I_{D} = -13 \text{ A},$		71	100	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -10 \text{ V}$		12		nC
Q_{gd}	Gate-Drain Charge			15		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				-2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -2.1 A (Note 2)		-0.7	-1.2	V

Notes

R_{0,1A} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0,0C} is guaranteed by design while R_{0,0CA} is determined by the user's board design.



a) 50°C/W (10 sec) 62.5°C/W steady state when mounted on a 1in² pad of 2 oz copper



b) 105°C/W when mounted on a .04 in² pad of 2 oz copper



c) 125°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < $300\mu s$, Duty Cycle < 2.0%

Typical Characteristics

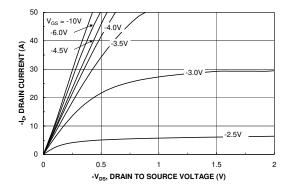


Figure 1. On-Region Characteristics.

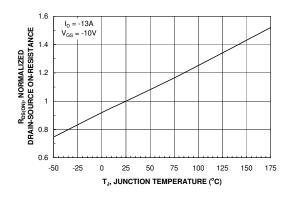


Figure 3. On-Resistance Variation with Temperature.

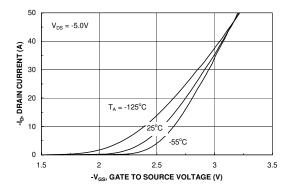


Figure 5. Transfer Characteristics.

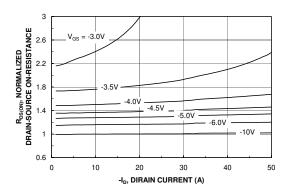


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

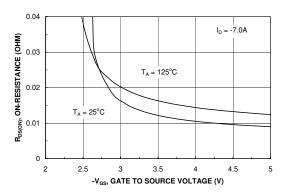


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

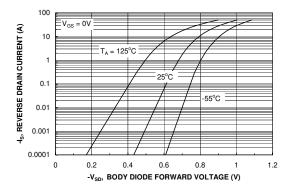
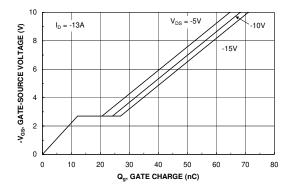


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



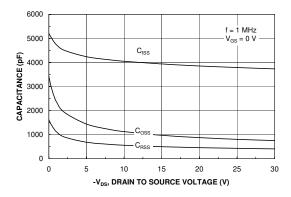
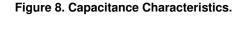
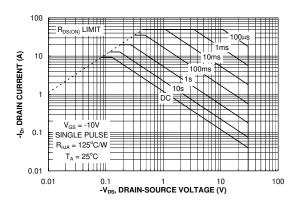


Figure 7. Gate Charge Characteristics.





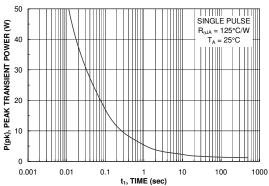


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

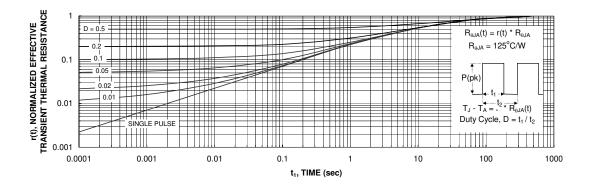


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hol

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative